
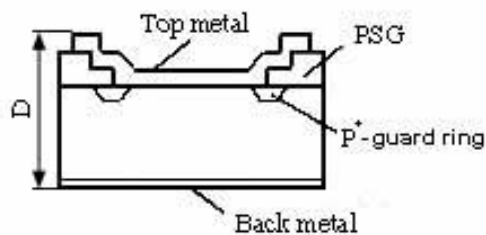
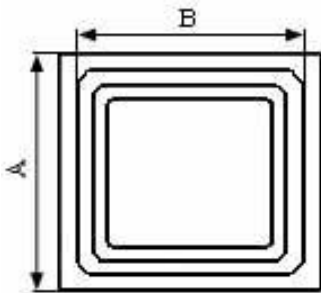


		3A/65V. Die Size-55mil.		
				
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_{BR}	V	65	68
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-
DC Forward Voltage @ 25°C, $I_F=3,0A$	V_F	V	0,64	0,62
Maximum Reverse Current @ 25°C, $V_R=68V$ @ 25°C, $V_R=65V$ @ 125°C, $V_R=65V$	I_R	mA	- 0,120 35,0	0,120 0,100 30,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	80	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<150°C$.	I_{RRM}	A	2,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	150	



DIM	ITEM	µm
A_x A_y	Wafer Form Die Size	1400 1400
B_x B_y	Top Metal Size	1260 1260
D	Thickness	300max.
	Scribe line Width	80

Top metal:

- a) **Al** – for Wire Bonding;
 - b) **Al-Ni-Ag** – for Soldering.
- Backside metal: **Ti-Ni-Ag**.